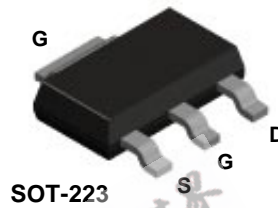
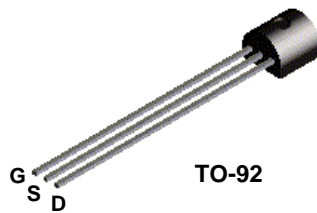


**J105  
J106  
J107**

**JFTJ105**



## N-Channel Switch

This device is designed for analog or digital switching applications where very low On Resistance is mandatory. Sourced from Process 59.

### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{DG}$	Drain-Gate Voltage	25	V
$V_{GS}$	Gate-Source Voltage	- 25	V
$I_{GF}$	Forward Gate Current	10	mA
$T_J, T_{Stg}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		J105 / J106 / J107	
$P_D$	Total Device Dissipation Derate above 25°C	350	mW
		2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

**N-Channel Switch**  
(continued)

**Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
--------	-----------	-----------------	-----	-----	-------

**OFF CHARACTERISTICS**

$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$I_G = -10 \mu A, V_{DS} = 0$	-25		V
$I_{GSS}$	Gate Reverse Current	$V_{GS} = -15 V, V_{DS} = 0$ $V_{GS} = -15 V, V_{DS} = 0, T_A = 100^\circ C$		-3.0 -200	nA nA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	$V_{DS} = 15 V, I_D = 10 nA$	<b>J105</b> <b>J106</b> <b>J107</b>	-4.5 -2.0 -4.5	V V V

**ON CHARACTERISTICS**

$I_{DSS}$	Zero-Gate Voltage Drain Current*	$V_{DS} = 15 V, I_{GS} = 0$	<b>J105</b> <b>J106</b> <b>J107</b>	500 200 100	mA mA mA
$r_{DS(on)}$	Drain-Source On Resistance	$V_{DS} \leq 0.1 V, V_{GS} = 0$	<b>J105</b> <b>J106</b> <b>J107</b>	3.0 6.0 8.0	$\Omega$ $\Omega$ $\Omega$

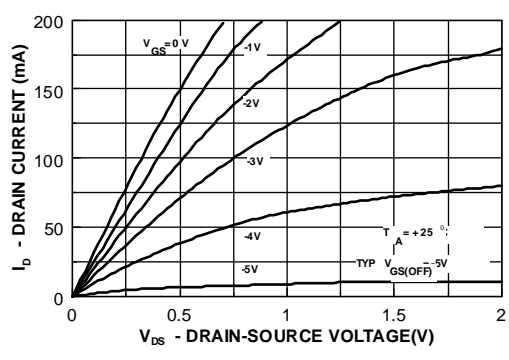
**SMALL SIGNAL CHARACTERISTICS**

$C_{dg(on)}$ $C_{sg(on)}$	Drain Gate & Source Gate On Capacitance	$V_{DS} = 0, V_{GS} = 10 V, f = 1.0 MHz$		160	pF
$C_{dg(off)}$	Drain-Gate Off Capacitance	$V_{DS} = 0, V_{GS} = 10 V, f = 1.0 MHz$		35	pF
$C_{sg(off)}$	Source-Gate Off Capacitance	$V_{DS} = 0, V_{GS} = 10 V, f = 1.0 MHz$		35	pF

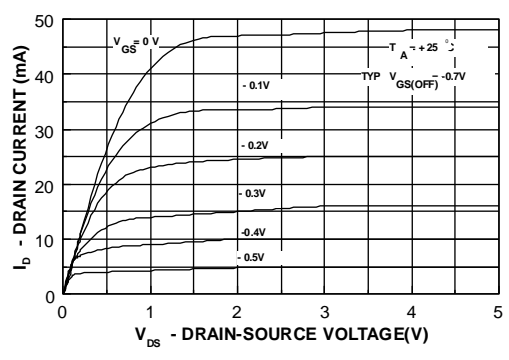
\*Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2.0\%$

**Typical Characteristics**

**Common Drain-Source Characteristics**

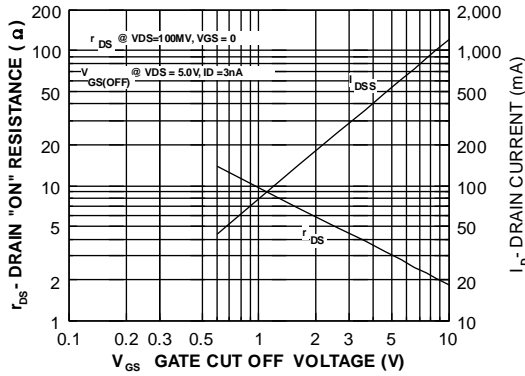


**Common Drain-Source Characteristics**

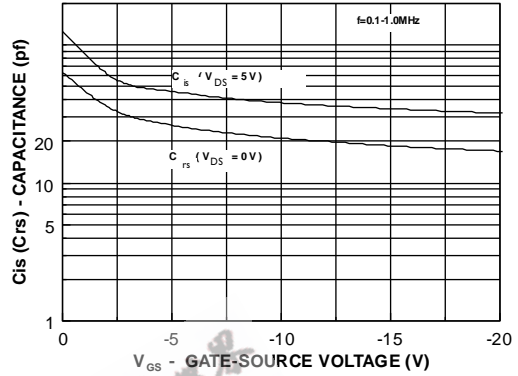


Typical Characteristics (continued)

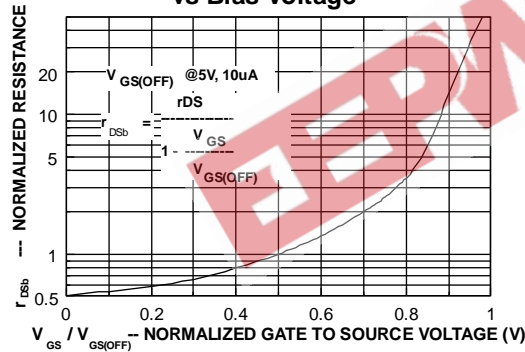
Parameter Interactions



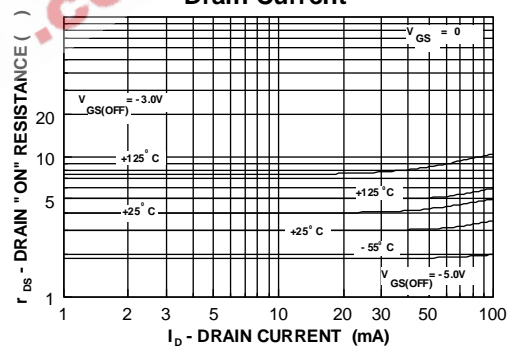
Capacitance vs Voltage



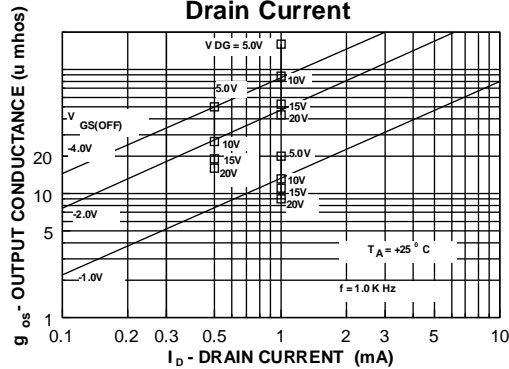
Normalized Drain Resistance vs Bias Voltage



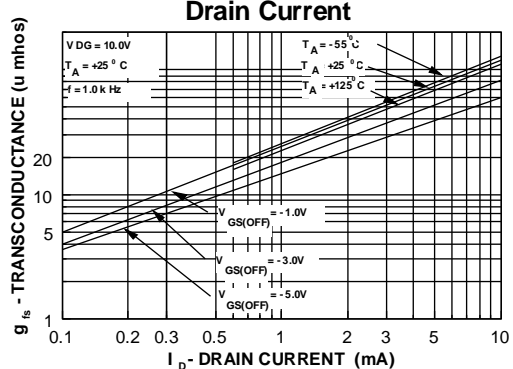
On Resistance vs Drain Current



Output Conductance vs Drain Current

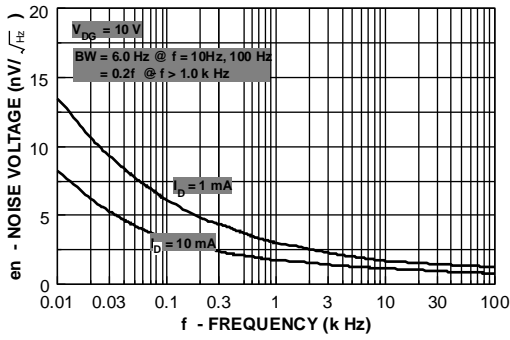


Transconductance vs Drain Current

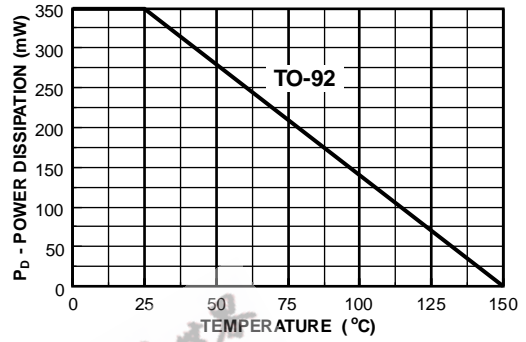


Typical Characteristics (continued)

Noise Voltage vs Frequency



Power Dissipation vs Ambient Temperature



EEPW.com.cn 电子產品世界